

NAVOLCHI

Victor Calzadilla

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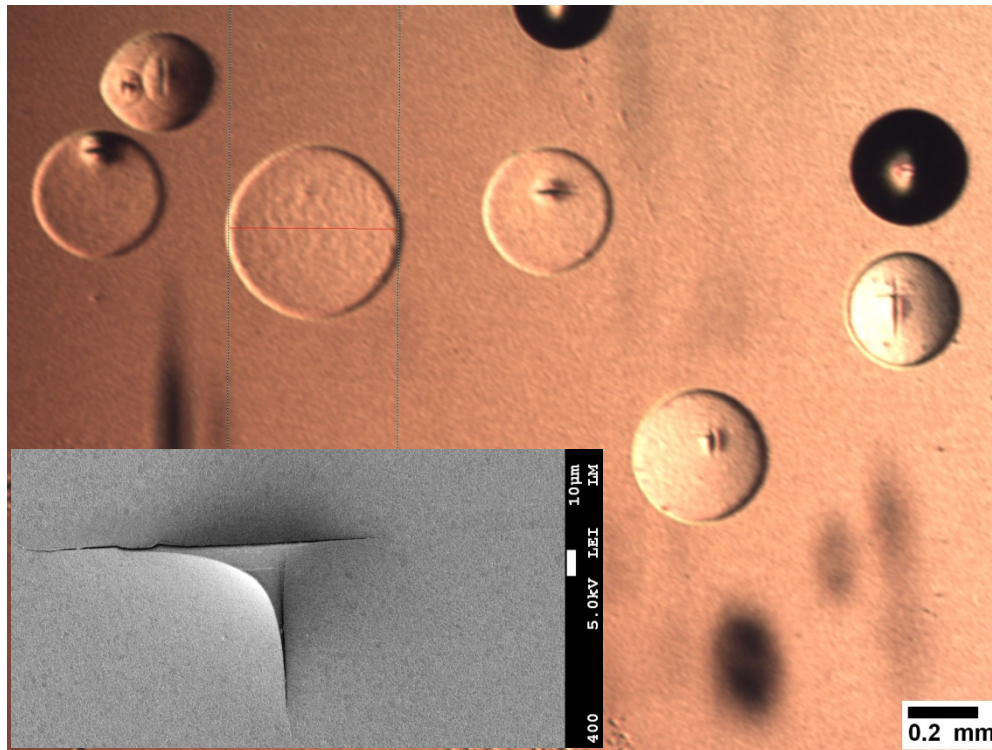
TU / **e**

Technische Universiteit
Eindhoven
University of Technology

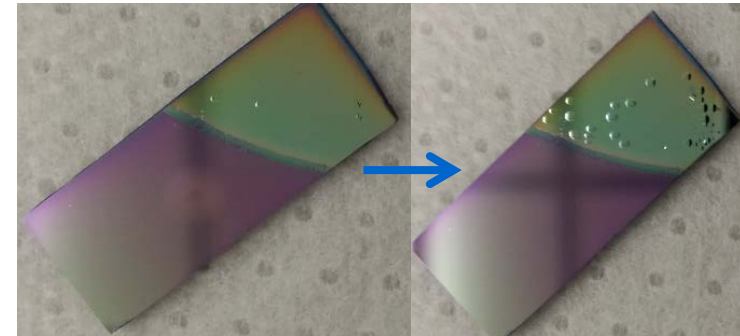
Where innovation starts

Investigation of outgassing in III-V membranes

- For $T \geq 300C$
 - Defects (tens/hundreds of μm)



After RTA, 400C, 15s

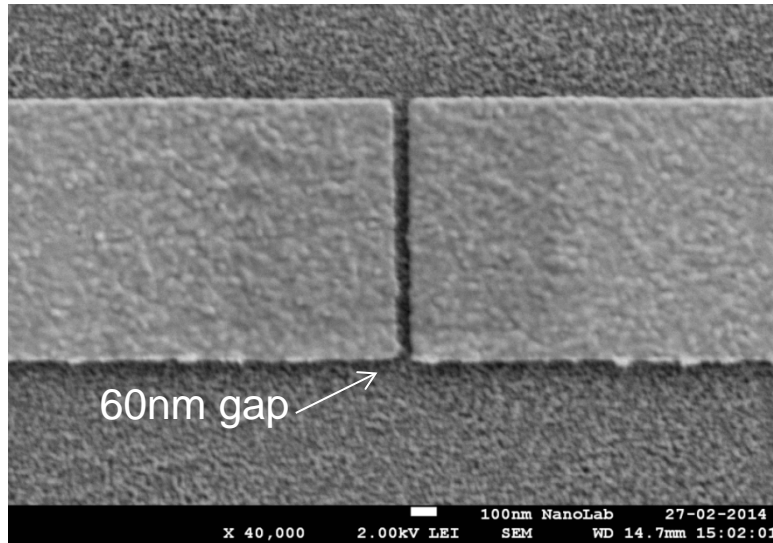


Layer stack:
Ag(300nm)
Ge(2nm)
SiO_x(200nm)
InP(270nm)
Bonding
Si-substrate

- What follows? Experiments of bondings done at high temperatures (350C)

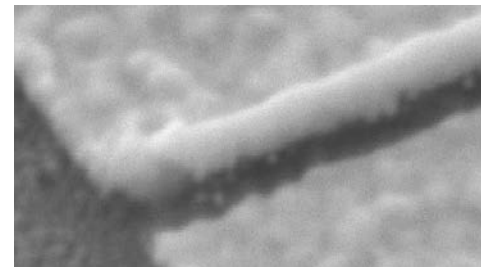
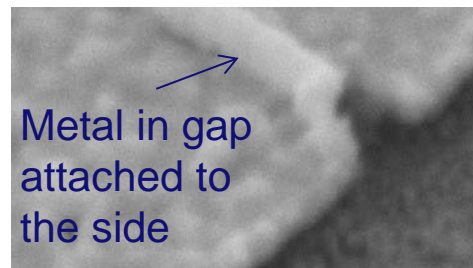
Nanogap for Valencia

- Dose test



- Achieved:
 - Line width = 100nm – 1um
 - Gap: 60nm - 220nm
 - Thickness = 50nm

- 1st attempt in real sample/pattern



- Can Valencia send more samples?

